# MICROWAVE POWER GaN HEMT TGI1314-25LA

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

#### **FEATURES**

**·BROAD BAND INTERNALLY MATCHED HEMT** 

- HIGH POWER
- Pout= 44.0dBm at Pin= 39.0dBm

#### ·HIGH GAIN

GL= 8.0dB at 13.75GHz to 14.5GHz

-LOW INTERMODULATION DISTORTION WITH WIDE SPACING TONE

IM3(Min.)= -25dBc at Pout= 37.0dBm (Single Carrier Level)

·HERMETICALLY SEALED PACKAGE



### RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power	Pout	VDS= 24V IDSset= 1.0A f =13.75 to 14.5GHz @Pin= 39dBm	dBm	43.0	44.0	
Drain Current	IDS1		A		2.5	3.0
Power Added Efficiency	PAE		%		29	_
Linear Gain	GL	- @Pin= 20dBm	dB	7.0	8.0	_
Gain Flatness	ΔG		dB			±0.8
3rd Order Intermodulation Distortion	IM3	Two-tone Test Po= 37.0dBm (Single Carrier Level) ∆f= 5MHz (IM3) ∆f= 150MHz (IM3-2)	dBc	-25	-27	
	IM3-2		dBc	-25	-27	
Drain Current	IDS2		A		1.75	2.25
Channel Temperature Rise	∆Tch	(VDS X IDS + Pin – Pout) X Rth(c-c)	°C		110	140

Recommended Gate Resistance(Rg): 13.3 Ω

### ELECTRICAL CHARACTERISTICS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 5V IDS= 2.5A	S	_	2.25	_
Pinch-off Voltage	VGSoff	VDS= 5V IDS= 11.5mA	V	-1.0	-4.0	-6.0
Saturated Drain Current	IDSS	VDS= 5V VGS= 0V	A	_	9.0	
Gate-Source Breakdown Voltage	VGSO	IGS= -5mA	V	-10		
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W	_	2.8	3.2

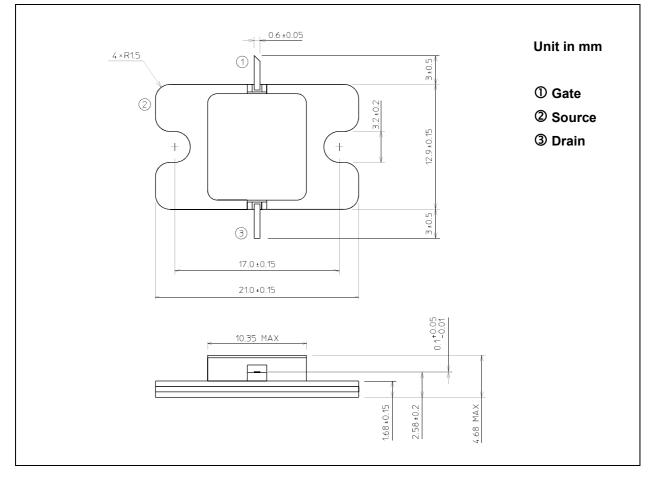
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### ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	50
Gate-Source Voltage	VGS	V	-10
Drain Current	IDS	А	7.5
Total Power Dissipation (Tc= 25°C)	PT	W	70
Channel Temperature	Tch	°C	250
Storage Temperature	Tstg	°C	-65 to +175

### PACKAGE OUTLINE (7-AA07A)



### HANDLING PRECAUTIONS FOR PACKAGE MODEL

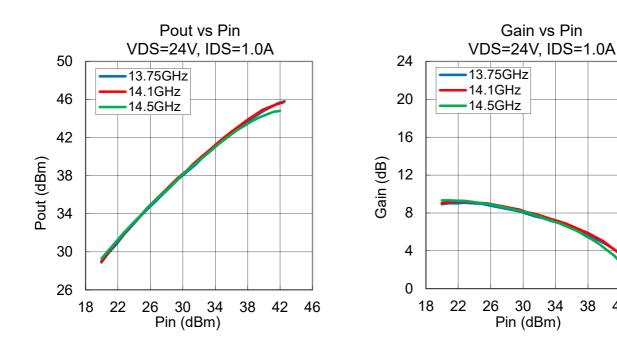
Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds at 350°C.

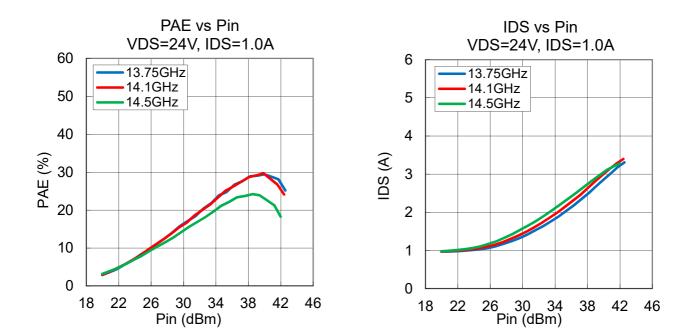
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#### MICROWAVE SEMICONDUCTOR TECHNICAL DATA

#### ·Pout , Gain , PAE , IDS vs. Pin

VDS= 24 V, IDSset= 1.0 A, f= 13.75, 14.1, 14.5 GHz, Ta= +25 °C





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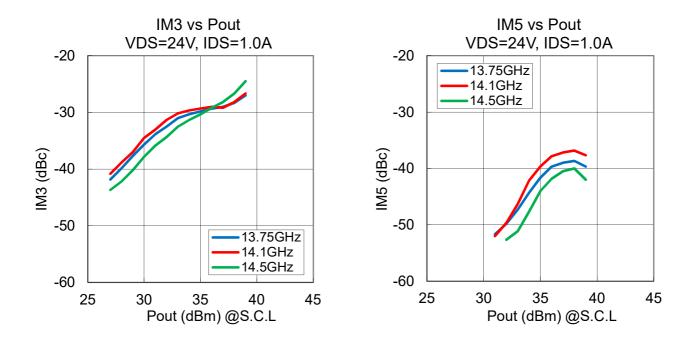
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MICROWAVE SEMICONDUCTOR TECHNICAL DATA

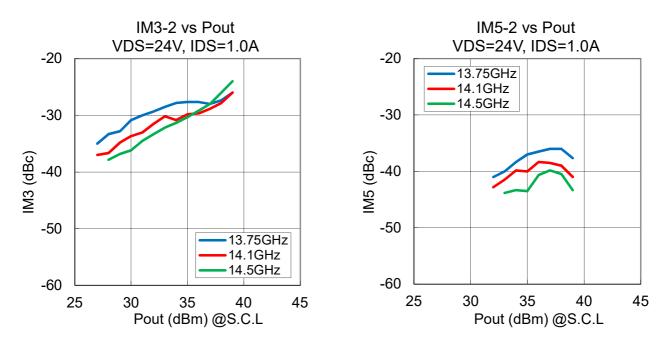
#### ·IM3, IM5 vs. Pout

VDS= 24 V, IDSset= 1.0 A, f= 13.75, 14.1, 14.5 GHz,  $\Delta$ f= 5 MHz , Ta= +25  $^{\circ}$ C



·IM3-2, IM5-2 vs. Pout

VDS= 24 V, IDSset= 1.0 A, f= 13.75, 14.1, 14.5 GHz,  $\Delta$ f= 150 MHz , Ta= +25  $^\circ$ C

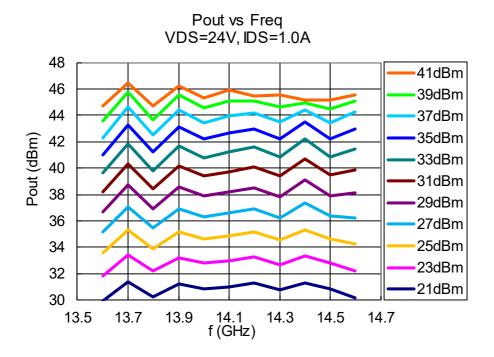


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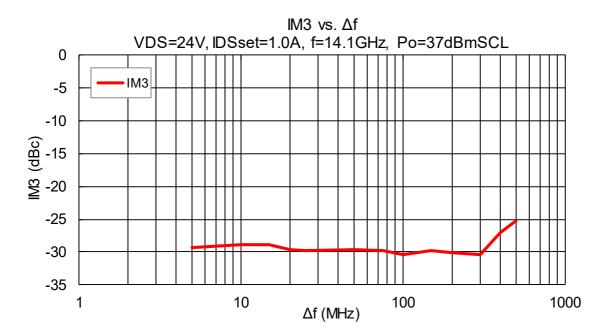
#### ·Pout vs. Frequency

VDS= 24 V, IDSset= 1.0 A, Ta= +25 °C



<sup>·</sup>IM3 vs. ∆f (Two tone spacing)

VDS= 24V, IDSset= 1.0A, f= 14.1GHz, Po= 37dBmSCL, Ta= +25°C

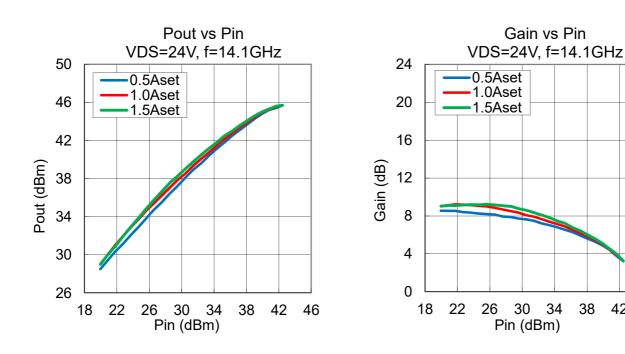


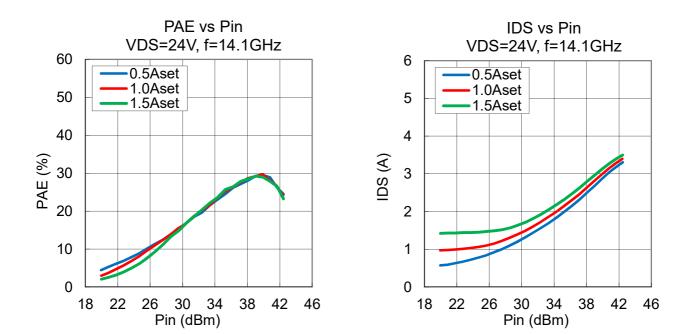
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ROWAVE SEMICONDUCTOR TECHNICAL DATA

#### ·Pout, Gain, PAE, IDS vs. Pin vs. IDSset

VDS= 24 V, IDSset= 0.5, 1.0, 1.5 A, f= 14.1 GHz, Ta= +25 °C





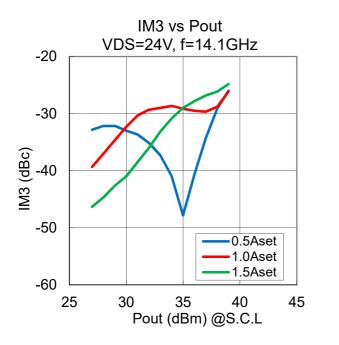
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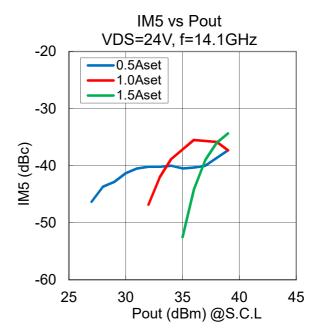
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MICROWAVE SEMICONDUCTOR TECHNICAL DATA

#### ·IM3, IM5 vs. Pout vs. IDSset

VDS= 24 V, IDSset= 0.5, 1.0, 1.5 A, f= 14.1 GHz,  $\Delta$ f= 5 MHz, Ta= +25 °C

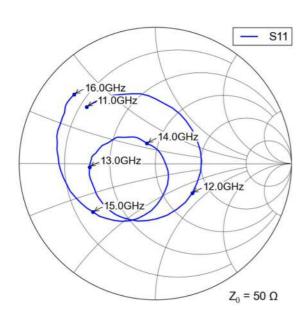


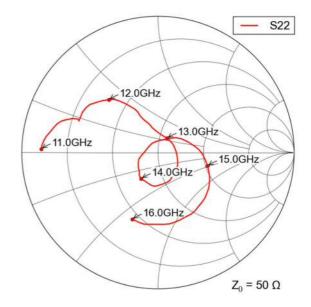


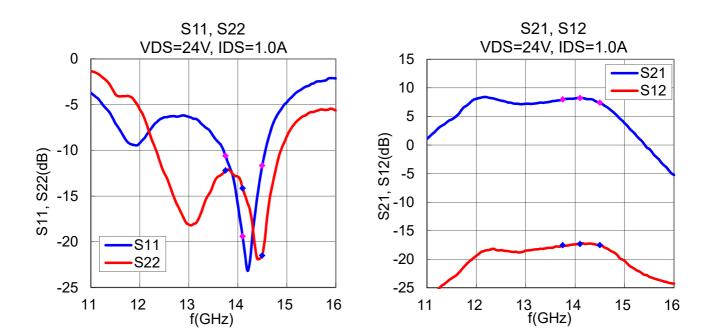
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#### ·S-Parameters

VDS= 24 V, IDSset= 1.0 A, f= 11.0 to 16.0 GHz, Ta= +25 ℃







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